

Title (en)
Method for treating semiconductor material

Title (de)
Verfahren zum Behandeln von Halbleitermaterial

Title (fr)
Procédé de traitement de matériau semiconducteur

Publication
EP 0976457 A1 20000202 (DE)

Application
EP 99113591 A 19990708

Priority
DE 19834447 A 19980730

Abstract (en)
For the processing of semiconductor materials, such as for the prodn. of solar cells, the semiconductor rods (1) of polycrystalline silicon are in a liquid medium and are subjected to shock waves from an energy converter (4). The energy converter is at a gap of 1-100 cm from the semiconductor rods. The shock waves from an arc between electrodes (8), through an elastic membrane (7), have a pulse energy of 1-20 kJ and a pulse increase time of 1-5 μ s to the max. energy level. The energy converter is a semi-ellipsoid reflector. The working surfaces of the transport and positioning units are of plastics to prevent any soiling of the semiconductor materials. The inner surfaces of the chamber are coated with plastics, where the semiconductor materials are broken down.

IPC 1-7
B02C 19/18

IPC 8 full level
B02C 19/00 (2006.01); **B02C 19/18** (2006.01); **B02C 23/36** (2006.01); **B28D 5/00** (2006.01); **C30B 29/06** (2006.01)

CPC (source: EP US)
B02C 19/18 (2013.01 - EP US); **B28D 5/0005** (2013.01 - EP US); **B02C 2019/183** (2013.01 - EP US)

Citation (applicant)
• EP 0573855 A1 19931215 - WACKER CHEMITRONIC [DE]
• US 5464159 A 19951107 - WOLF ANDREAS [DE], et al

Citation (search report)
• [AD] EP 0573855 A1 19931215 - WACKER CHEMITRONIC [DE]
• [AP] DE 19749127 A1 19990520 - WACKER CHEMIE GMBH [DE]
• [A] WO 8606652 A1 19861120 - CEEE CORP [US]
• [A] DE 19545579 A1 19970612 - TZN FORSCHUNG & ENTWICKLUNG [DE]
• [A] US 5082502 A 19920121 - LEE KAM B [US], et al

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